

BCR2PM-12

Triac

Low Power Use

REJ03G0300-0100

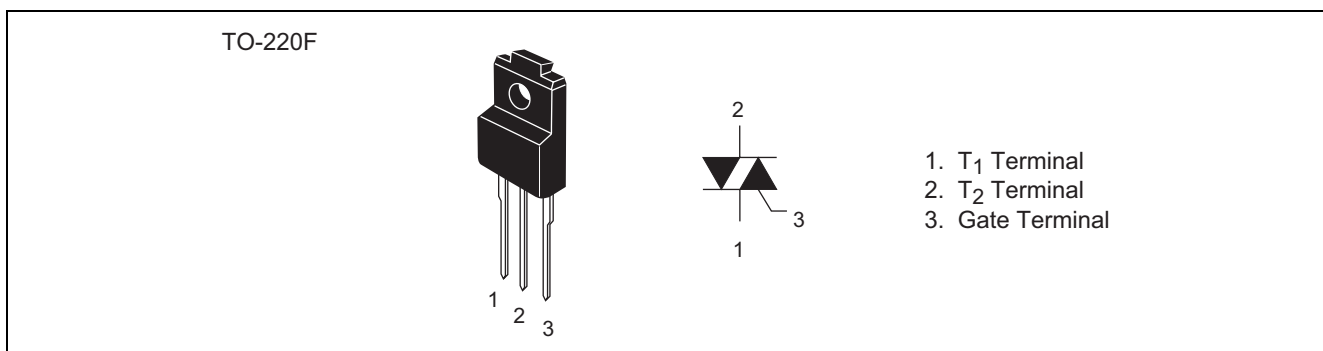
Rev.1.00

Aug.20.2004

Features

- $I_{T(RMS)}$: 2 A
- V_{DRM} : 600 V
- I_{RGTI}, I_{RGTIII} : 10 mA
- Non-Insulated Type
- Planar Passivation Type

Outline



Applications

Electric rice cooker, electric pot, and controller for other heater

Precautions on Usage

When the BCR2PM-12 is used, do not attach the heat radiating fin.

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	600	V
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	720	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_T (RMS)$	2	A	Commercial frequency, sine full wave 360° conduction
Surge on-state current	I_{TSM}	10	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	0.41	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	1	W	
Average gate power dissipation	$P_{G(AV)}$	0.1	W	
Peak gate voltage	V_{GM}	6	V	
Peak gate current	I_{GM}	1	A	
Junction temperature	T_j	- 40 to +125	°C	
Storage temperature	T_{stg}	- 40 to +125	°C	
Mass	—	2.0	g	Typical value

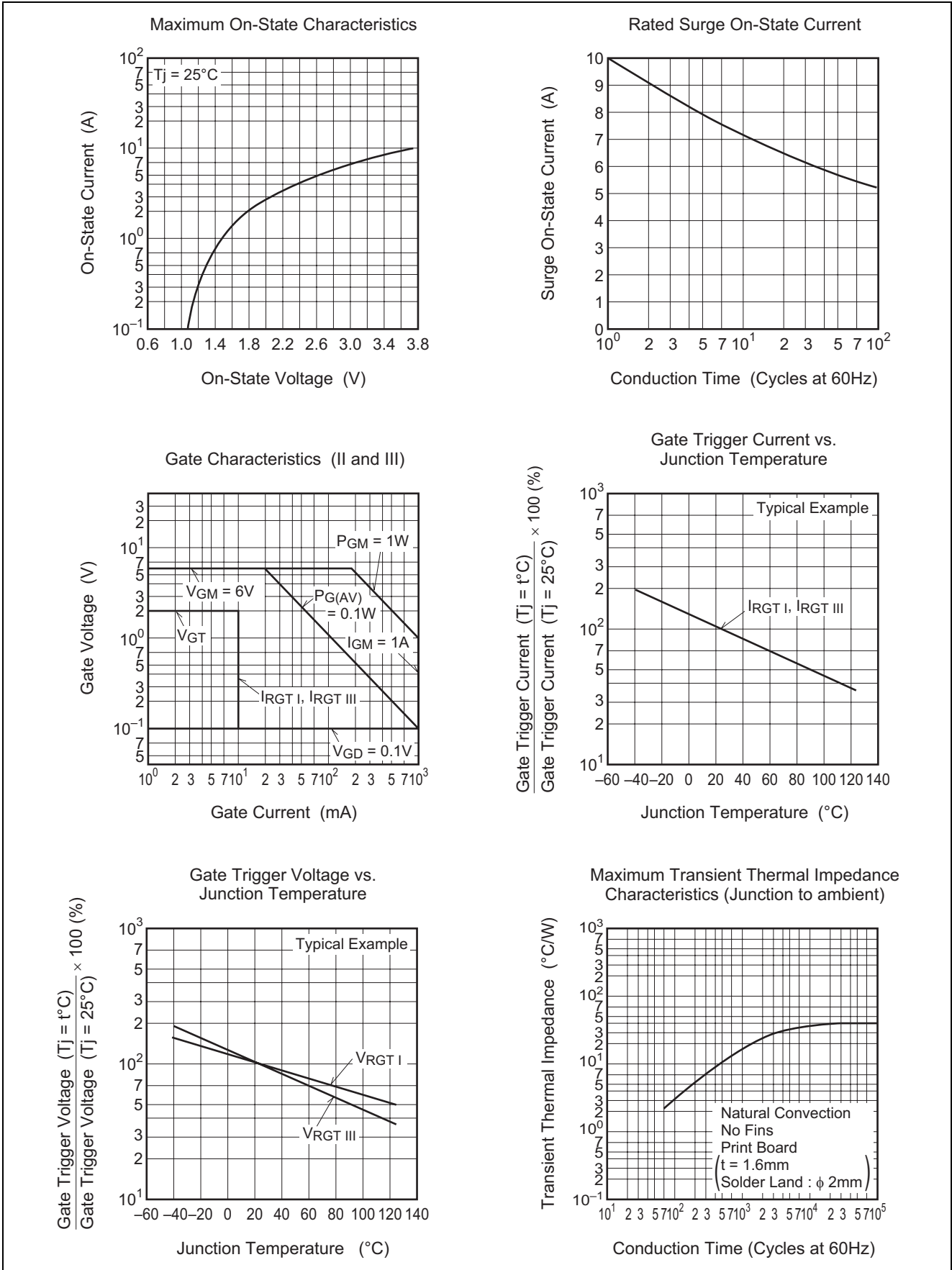
Notes: 1. Gate open.

Electrical Characteristics

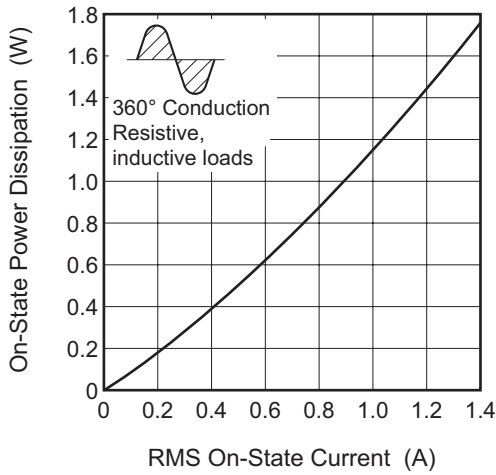
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current	I_{DRM}	—	—	0.5	mA	$T_j = 125^\circ\text{C}$, V_{DRM} applied
On-state voltage	V_{TM}	—	—	1.6	V	$T_j = 25^\circ\text{C}$, $I_{TM} = 1.5\text{ A}$, Instantaneous measurement
Gate trigger voltage ^{Note2}	II	V_{RGTI}	—	—	2.0	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	III	V_{RGTIII}	—	—	2.0	
Gate trigger current ^{Note2}	II	I_{RGTI}	—	—	10	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	III	I_{RGTIII}	—	—	10	
Gate non-trigger voltage	V_{GD}	0.1	—	—	V	$T_j = 125^\circ\text{C}$, $V_D = 1/2 V_{DRM}$
Thermal resistance	$R_{th(j-a)}$	—	—	40	°C/W	Junction to ambient, Natural convection

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

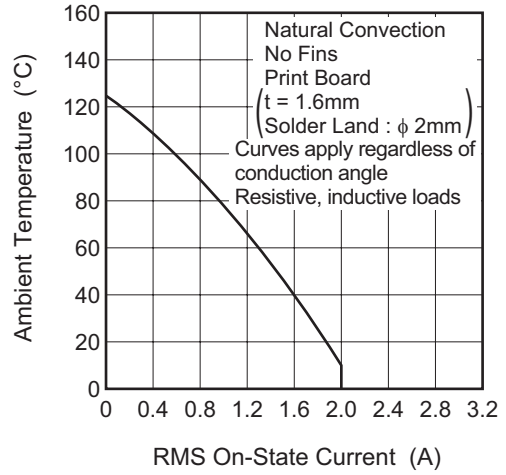
Performance Curves



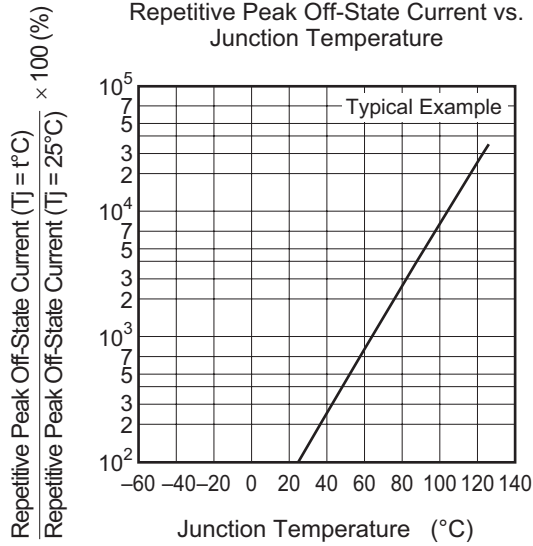
Maximum On-State Power Dissipation



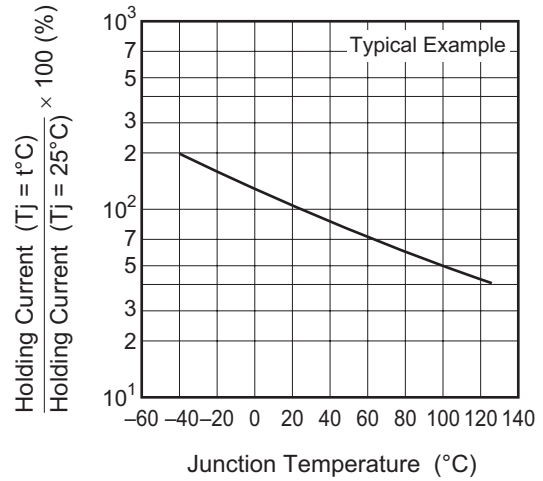
Allowable Ambient Temperature vs. RMS On-State Current



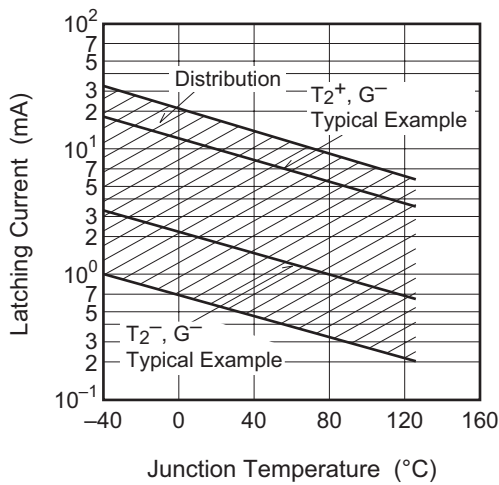
Repetitive Peak Off-State Current vs. Junction Temperature



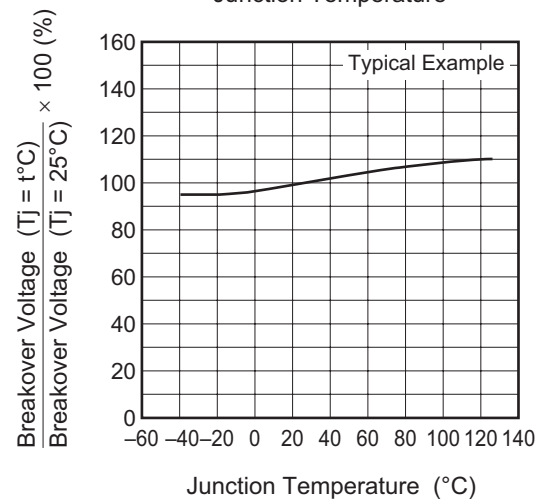
Holding Current vs. Junction Temperature



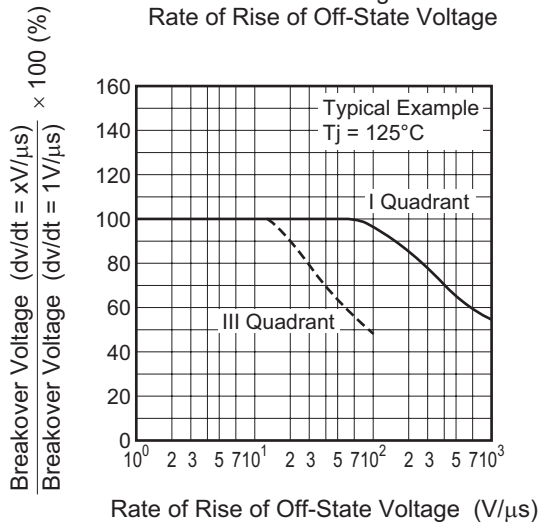
Latching Current vs. Junction Temperature



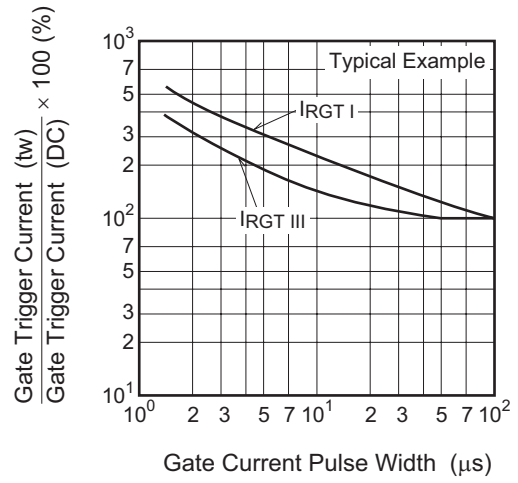
Breakover Voltage vs. Junction Temperature



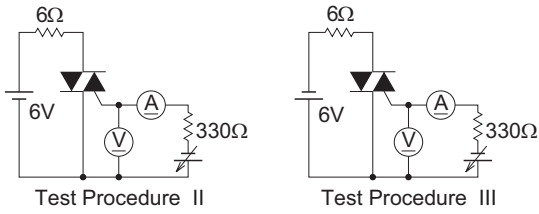
Breakover Voltage vs. Rate of Rise of Off-State Voltage



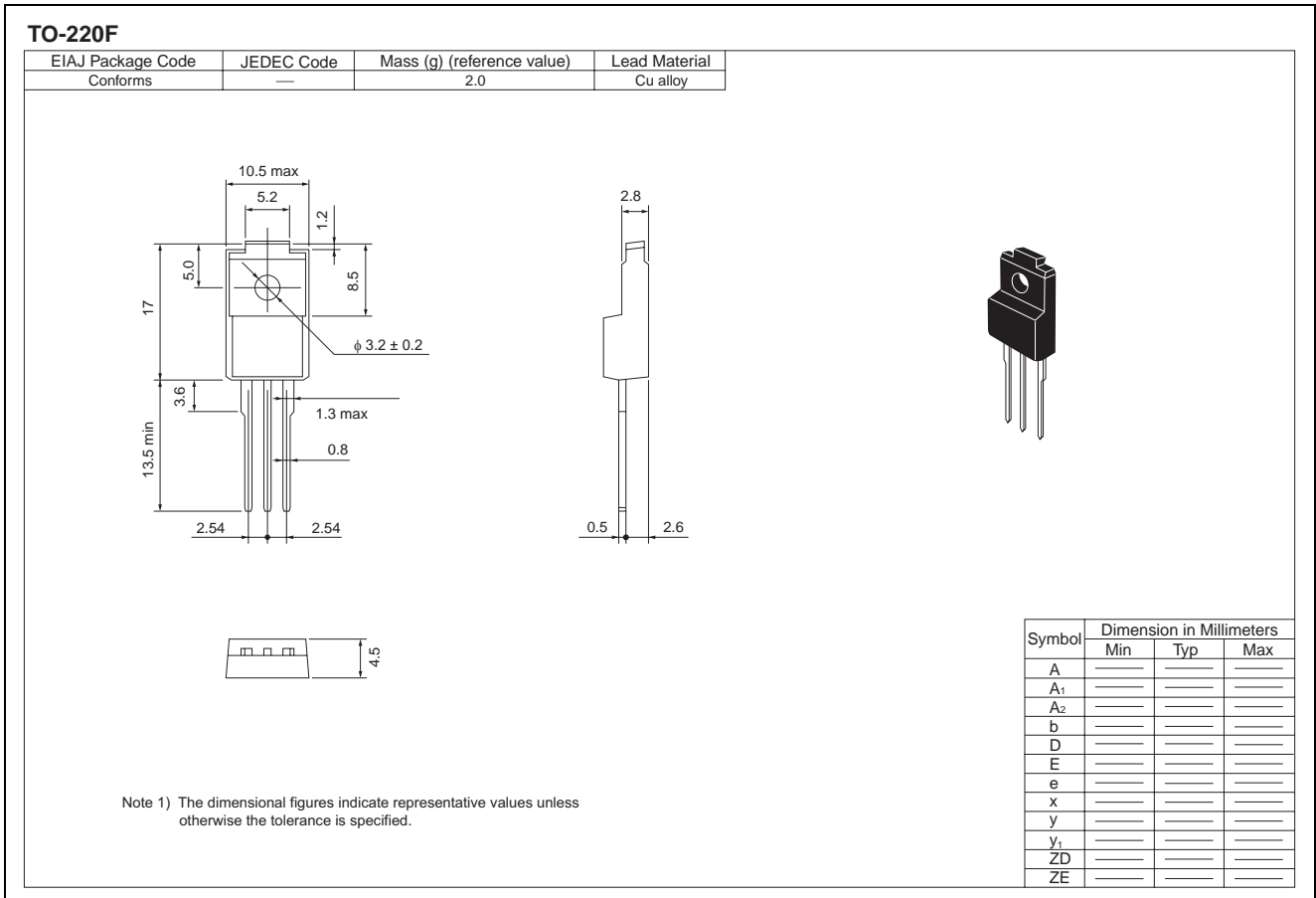
Gate Trigger Current vs. Gate Current Pulse Width



Gate Trigger Characteristics Test Circuits



Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name +RA	BCR2PM-12RA
Lead form	Plastic Magazine (Tube)	50	Type name +RA – Lead forming code	BCR2PM-12RA-A8

Note : Please confirm the specification about the shipping in detail.

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